TEXAS INSTRUMENTS

CD40106B Types

Data sheet acquired from Harris Semiconductor SCHS097

CMOS Hex Schmitt Triggers

High-Voltage Types (20-Volt Rating)

■ CD40106B consists of six Schmitttrigger circuits. Each circuit functions as an inverter with Schmitt-trigger action on the input. The trigger switches at different points for positive- and negative-going signals. The difference between the positive-going voltage (VP) and the negative-going voltage (VN) is defined ashysteresis voltage (VH) (see Fig.6). The CD40106B types are supplied in 14lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).

Features:

- Schmitt-trigger action with no external components
 Hysteresis voltage (typ.) 0.9 V at V_{DD} = 5 V, 2.3 V at
- V_{DD} = 10 V, and 3.5 V at V_{DD} = 15 V
- Noise immunity greater than 50%
- No limit on input rise and fall times
 Standardized symmetrical output chara
- Standardized, symmetrical output characteristics
 100% tested for quiescent current at 20 V
- Maximum input current of 1 µA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Low VDD to VSS current during slow input ramp
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators

MAXIMUM RATINGS, Absolute-Maximum Values:
DC SUPPLY-VOLTAGE RANGE, (VDD)
Voltages referenced to VSS Terminal)
INPUT VOLTAGE RANGE, ALL INPUTS
DC INPUT CURRENT, ANY ONE INPUT ±10mA
POWER DISSIPATION PER PACKAGE (PD):
For $T_A = -55^{\circ}C$ to $+100^{\circ}C$
For $T_A = +100^{\circ}C$ to $+125^{\circ}C$ Derate Linearity at $12 \text{mW/}^{\circ}C$ to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)
OPERATING-TEMPERATURE RANGE (T _A)55°C to +125°C
STORAGE TEMPERATURE RANGE (Tstg)65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10s max +265°C

RECOMMENDED OPERATING CONDITIONS

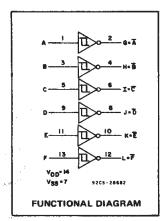
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

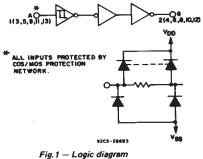
	LIN	UNITS		
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For TA Full Package-Temperature Range)	3	18	Ŷ	

DYNAMIC ELECTRICAL CHARACTERISTICS

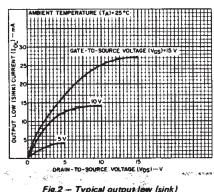
At $T_A = 25^{\circ}C$, Input t_r , $t_f = 20 \text{ ns}$, $C_L = 50 \text{ pF}$, $R_L = 200 \text{ k}\Omega$

	TEST COND	ITIONS	LI	LIMITS			
CHARACTERISTIC	VDD (V)		TYP.	MAX.	UNITS		
Propagation Delay Time:		5	140	280			
tPHL,		10	70	140	i ns.		
^t PLH		15	60	120	ja silit		
Transition Time:		5	100	200			
tTHL,		10	50	100	ns		
TLH		15	40	80			
Input Capacitance, CIN	Any Input		5	7.5	pF		

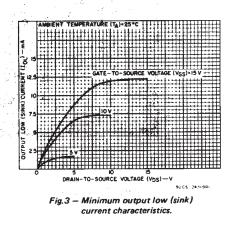




(1 of 6 Schmitt triggers).

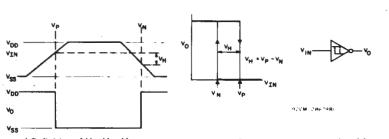


current characteristics.

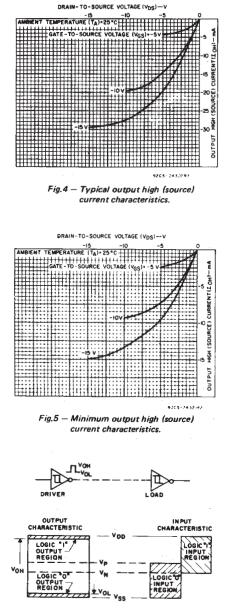


STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	co Vo	NDITI		LIMI	LIMITS AT INDICATED TEMPERATURES (°C)						
	(V)	VIN (V)	VDD (V)	-55	-40	+85	+125	Min.	+25 Typ.	Mex.	-
Quiescent Device Current, IDD Max.	. <u>_</u>	0,5	5	1	1	30	30		0.02	1	μА
	-	0,10	10	2	2	60	60	-	0.02	2	
	-	0,15	15	4	4	120	120	-	0.02	4	
	-	0,20	20	20	20	600	600	-	0.04	20	1
Positive Trigger	_	-	5	2.2	2.2	2.2	2.2	2.2	2.9	- 1	
Threshold Voltage	-		10	4.6	4.6	4.6	4.6	4.6	5.9	-	1
V _p Min.	-	-	15	6.8	6.8	6.8	6.8	6.8	8.8		1
	-	-	5	3.6	3.6	3.6	3.6	-	2.9	3.6	V.
Vp Max.	-	_	10	7.1	7.1	7.1	7.1	-	5.9	7.1	1
F	-	-	15	10.8	10.8	10.8	10.8	-	8.8	.10,8	1
Negative Trigger		-	5	0.9	0.9	0.9	0.9	0.9	1.9	-	<u> </u>
Threshold Voltage	_		10	2.5	2.5	2.5	2.5	2.5	3.9	_	1
V _N Min.	-	-	15	4	4	4	4	4	5.8	-	
		-	5	2.8	2.8	2.8	2.8		1.9	2.8	· ·
V _N Max.	-	. –	10	5.2	5.2	5.2	5.2	-	3.9	5.2	
	-		15	7.4	7.4	7.4	7.4		5.8	7.4	
	-		5	0.3	0.3	0.3	0.3	0.3	0.9	-	v
Hysteresis Voltage	-	-	10	1.2	1.2	1.2	1.2	1.2	2.3	-	
V _H Min.	-		15	1.6	1.6	1.6	1.6	1.6	3.5	-	
		_	5	1.6	1.6	1.6	1.6	-	0.9	1.6	
V _H Max.	-	-	10	3.4	3.4	3.4	3.4	_	2.3	3.4	
	1	_	15	5	5	5	5	-	3.5	5	
Output Low (Sink)	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	_	
Current,	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	1
Output High	4.6	0,5	5	0.64	-0.61	-0.42	-0.36	-0.51	-1		mA
(Source)	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
Current, IOH Min.	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0,15	15	-4.2	4	2.8	-2.4	-3.4	-6.8		
Output Voltage	_	5	5		0.	05		-	0	0.05	
Low-Level, VOL Max.	-	10	10	0.05 - 0 0.					0.05	0.05	
	-	15	15		0.	05		-	0	0.05	v
Output Voltage		0	5		4.9	95		4.95	5	_	v
High Level,	-	0	10		9.	95		9.95	10	-	1
VOH Min.		0	15		14	.95		14.95	15		
Input Current, IIN Max.		0,18	18	±0.1	±0.1	±1	±1	_	±10-5	±0.1	μA



a) Definition of Vp, V_N, V_H b) Transfer characteristics of 1 of 6 gates Fig.6 - Hysteresis definition, characteristics, and test set-up.

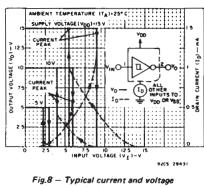


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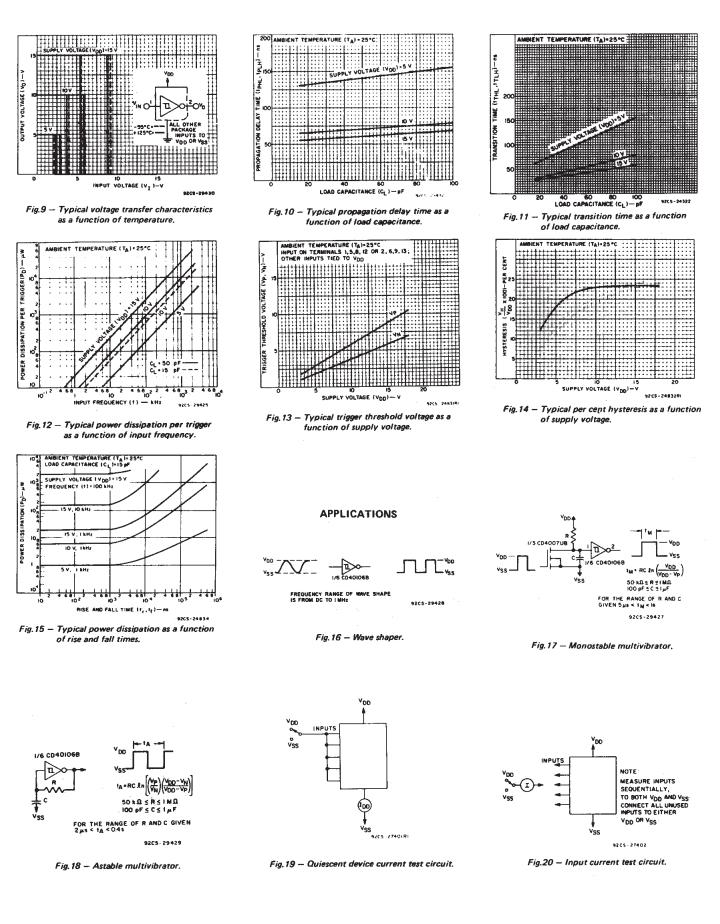
COMMERCIAL CMOS HIGH VOLTAGE ICs





transfer characteristics.

CD40106B Types



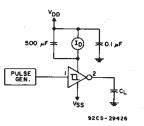
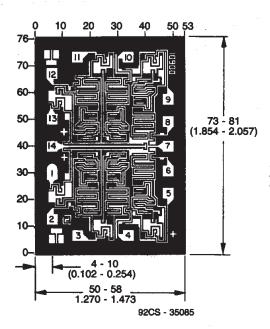


Fig.21 - Dynamic power dissipation test circuit.

TERMINAL ASSIGNMENT



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and Pad Layout for CD40106BH

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